

INFORMATION DISCLOSURE CITATION <i>(Use several sheets if necessary)</i>				Docket Number (Optional) Y0R920030293US1 (16818)	Application Number 10/674,647		
				Applicant(s) Kwang Su Choe, et al.			
				Filing Date September 30, 2003	Group Art Unit 1753 - 1762		
U.S. PATENT DOCUMENTS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
U.S. PATENT APPLICATION PUBLICATIONS							
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
/MLP/		US 2002/0086463 A1	07/04/02	Houston, et al	—	—	
/MLP/		US 2004/0126985 A1	07/01/04	Bendernagel, et al	—	—	
FOREIGN PATENT DOCUMENTS							
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation
							YES NO
/MLP/		9-64323	07/03/97	Japan	—	—	X
/MLP/		WO 2005/034209 A2	04/15/05	PCT	—	in English	
OTHER DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>							
/MLP/		Matsumura, et al., "Technological innovation in low-dose SIMOX wafers fabricated by an internal thermal oxidation (ITOX) process", 2002 Elsevier Science B.V., Microelectronic Engineering 66 (2003), pp. 400-414 all odd-numbered pages missing no month					
		<i>[Signature]</i> 6/1/2007					
EXAMINER	/Mariahne L. Padgett/		DATE CONSIDER				
			05/18/2007				
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							